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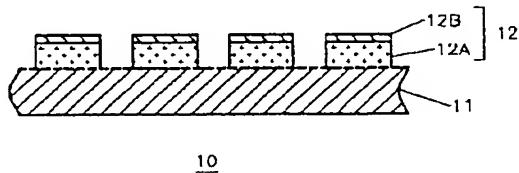
(54) TRANSFER BUMP SUBSTRATE AND METHOD
OF TRANSFERRING BUMP

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(57) Abstract:

PROBLEM TO BE SOLVED: To eliminate various problems such as the deviation in position of conductive bumps due to small force, vibration, or the like because the conductive bumps are floated on a molten low-temperature solder layer when being transferred onto a silicon chip, a narrow choice of solders because a combination of the low-temperature solder layer and a high-temperature solder layer must be considered, a difficult and dangerous job for separating the silicon chip and substrate from each other because the whole body is kept at 200°C or above during the job, and the destruction of the silicon chip which often occurs when the silicon chip and substrate are separated from each other.

SOLUTION: In this transfer bump substrate 10, a resin film or soft resin plate is used for a substrate 11. A copper layer 12A is formed directly on the substrate 11 rather than through the low-temperature solder layer, and a solder layer 12B is formed on the copper layer 12A.



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